



SI3445DV-T1-E3 Information



For Reference Only

Part Number SI3445DV-T1-E3
Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET P-CH 8V 6-TSOP **Package** SOT-23-6 Thin, TSOT-23-6

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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SI3445DV-T1-E3 Specifications

Manufacturer Part NumberSI3445DV-T1-E3ManufacturerVishay SiliconixCategoryDiscrete Semiconductor Products Transistors - FETs, MOSFETs - SinglePackageSOT-23-6 Thin, TSOT-23-6SeriesTrenchFET?FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)8VCurrent - Continuous Drain (Id) @ 25°C-Drive Voltage (Max Rds On, Min Rds On)1.8V, 4.5VVgs(th) (Max) @ Id1V @ 250µAGate Charge (Qg) (Max) @ Vgs25nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds±8VYgs (Max)±8VFET Feature-Power Dissipation (Max)2W (Ta)Rds On (Max) @ Id, Vgs42 mOhm @ 5.6A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package6-TSOPPackage / CaseSOT-23-6 Thin, TSOT-23-6Report errors?		
CategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageSOT-23-6 Thin, TSOT-23-6SeriesTrenchFET?FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)8VCurrent - Continuous Drain (Id) @ 25°C-Drive Voltage (Max Rds On, Min Rds On)1.8V, 4.5VVgs(th) (Max) @ Id1V @ 250μAGate Charge (Qg) (Max) @ Vgs25nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±8VFET Feature-Power Dissipation (Max)2W (Ta)Rds On (Max) @ Id, Vgs42 mOhm @ 5.6A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package6-TSOPPackage / CaseSOT-23-6 Thin, TSOT-23-6	Manufacturer Part Number	SI3445DV-T1-E3
Package SOT-23-6 Thin, TSOT-23-6 Series TrenchFET? FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 8V Current - Continuous Drain (Id) @ 25°C - Drive Voltage (Max Rds On, Min Rds On) 1.8V, 4.5V Vgs(th) (Max) @ Id 1V @ 250μA Gate Charge (Qg) (Max) @ Vgs 25nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) ±8V FET Feature - Power Dissipation (Max) 2W (Ta) Rds On (Max) @ Id, Vgs 42 mOhm @ 5.6A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 6-TSOP Package / Case SOT-23-6 Thin, TSOT-23-6	Manufacturer	Vishay Siliconix
Package SOT-23-6 Thin, TSOT-23-6 Series TrenchFET? FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 8V Current - Continuous Drain (Id) @ 25°C - Drive Voltage (Max Rds On, Min Rds On) 1.8V, 4.5V Vgs(th) (Max) @ Id 1V @ 250μA Gate Charge (Qg) (Max) @ Vgs 25nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds * Vgs (Max) ±8V FET Feature - Power Dissipation (Max) 2W (Ta) Rds On (Max) @ Id, Vgs 42 mOhm @ 5.6A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 6-TSOP Package / Case SOT-23-6 Thin, TSOT-23-6	Category	Discrete Semiconductor Products
Series TrenchFET? FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 8V Current - Continuous Drain (Id) @ 25°C - Drive Voltage (Max Rds On, Min Rds On) 1.8V, 4.5V Vgs(th) (Max) @ Id 1V @ 250µA Gate Charge (Qg) (Max) @ Vgs 25nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) ±8V FET Feature - Power Dissipation (Max) 2W (Ta) Rds On (Max) @ Id, Vgs 42 mOhm @ 5.6A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 6-TSOP Package / Case SOT-23-6 Thin, TSOT-23-6		Transistors - FETs, MOSFETs - Single
FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)8VCurrent - Continuous Drain (Id) @ 25°C-Drive Voltage (Max Rds On, Min Rds On)1.8V, 4.5VVgs(th) (Max) @ Id1V @ 250μAGate Charge (Qg) (Max) @ Vgs25nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±8VFET Feature-Power Dissipation (Max)2W (Ta)Rds On (Max) @ Id, Vgs42 mOhm @ 5.6A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package6-TSOPPackage / CaseSOT-23-6 Thin, TSOT-23-6	Package	SOT-23-6 Thin, TSOT-23-6
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)8VCurrent - Continuous Drain (Id) @ 25°C-Drive Voltage (Max Rds On, Min Rds On)1.8V, 4.5VVgs(th) (Max) @ Id1V @ 250μAGate Charge (Qg) (Max) @ Vgs25nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±8VFET Feature-Power Dissipation (Max)2W (Ta)Rds On (Max) @ Id, Vgs42 mOhm @ 5.6A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package6-TSOPPackage / CaseSOT-23-6 Thin, TSOT-23-6	Series	TrenchFET?
Drain to Source Voltage (Vdss)8VCurrent - Continuous Drain (Id) @ 25°C-Drive Voltage (Max Rds On, Min Rds On)1.8V, 4.5VVgs(th) (Max) @ Id1V @ 250μAGate Charge (Qg) (Max) @ Vgs25nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±8VFET Feature-Power Dissipation (Max)2W (Ta)Rds On (Max) @ Id, Vgs42 mOhm @ 5.6A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package6-TSOPPackage / CaseSOT-23-6 Thin, TSOT-23-6	FET Type	P-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 1.8V, 4.5V Vgs(th) (Max) @ Id 1V @ 250µA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) #8V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 42 mOhm @ 5.6A, 4.5V Operating Temperature Supplier Device Package Package / Case - Current - Continuous Drain (Id) @ 25°C - 1.8V, 4.5V - 55°C ~ 150°C (TJ) Surface Mount 6-TSOP Package / Case SOT-23-6 Thin, TSOT-23-6	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Surplier Device Package Package / Case 1 V @ 250μA 25nC @ 4.5V	Drain to Source Voltage (Vdss)	8V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case 1V @ 250μA 25nC @ 4.5V - - - - - - - - - - - - -	Current - Continuous Drain (Id) @ 25°C	-
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) ETF Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case SOT-23-6 Thin, TSOT-23-6	Drive Voltage (Max Rds On, Min Rds On)	1.8V, 4.5V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case SOT-23-6 Thin, TSOT-23-6	Vgs(th) (Max) @ Id	1V @ 250μA
Vgs (Max)±8VFET Feature-Power Dissipation (Max)2W (Ta)Rds On (Max) @ Id, Vgs42 mOhm @ 5.6A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package6-TSOPPackage / CaseSOT-23-6 Thin, TSOT-23-6	Gate Charge (Qg) (Max) @ Vgs	25nC @ 4.5V
FET Feature - Power Dissipation (Max) 2W (Ta) Rds On (Max) @ Id, Vgs 42 mOhm @ 5.6A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 6-TSOP Package / Case SOT-23-6 Thin, TSOT-23-6	Input Capacitance (Ciss) (Max) @ Vds	-
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 42 mOhm @ 5.6A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 6-TSOP Package / Case SOT-23-6 Thin, TSOT-23-6	Vgs (Max)	±8V
Rds On (Max) @ Id, Vgs42 mOhm @ 5.6A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package6-TSOPPackage / CaseSOT-23-6 Thin, TSOT-23-6	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 6-TSOP Package / Case SOT-23-6 Thin, TSOT-23-6	Power Dissipation (Max)	2W (Ta)
Mounting Type Surface Mount Supplier Device Package 6-TSOP Package / Case SOT-23-6 Thin, TSOT-23-6	Rds On (Max) @ Id, Vgs	42 mOhm @ 5.6A, 4.5V
Supplier Device Package 6-TSOP Package / Case SOT-23-6 Thin, TSOT-23-6	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case SOT-23-6 Thin, TSOT-23-6	Mounting Type	Surface Mount
	Supplier Device Package	6-TSOP
Report errors?	Package / Case	SOT-23-6 Thin, TSOT-23-6
		Report errors?

SI3445DV-T1-E3 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

SI3445DV-T1-E3 Payment Methods



















SI3445DV-T1-E3 Shipping Methods













If you have any question about SI3445DV-T1-E3, please do not hesitate to contact us!

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